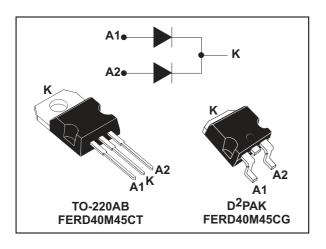


FERD40M45C

Field effect rectifier

Datasheet - production data



Features

- ST advanced rectifier process
- Stable leakage current over reverse voltage
- Low forward voltage drop
- High frequency operation

Description

This dual rectifier is based on a proprietary technology that achieves the best in class $V_{\rm F}/I_{\rm R}$ for a given silicon surface.

Packaged in TO-220AB, and D^2PAK , this device is intended to be used in switch mode power supplies, or automotive applications

Table 1. Device summary

I _{F(AV)}	2 x 20 A
V _{RRM}	45 V
V _F (typ)	0.34 V

This is information on a product in full production.

1 Characteristics

Table 2. Absolute ratings (limiting values, per diode at 25° C, unless otherwise stated)

Symbol	Para	Value	Unit		
V _{RRM}	Repetitive peak reverse voltage			45	V
I _{F(RMS)}	Forward rms current			40	Α
I _{F(AV)}	Average forward current, $\delta = 0.5$	T _c =150° C T _c =140° C	Per diode Per device	20 40	A
I _{FSM}	Surge non repetitive forward current	soidal	275	Α	
T _{stg}	Storage temperature range	-65 to + 175	°C		
	Maximum operating junction	TO-220AB, D ² PA	АК	175	
Тj	temperature ⁽¹⁾		D ² PAK (DC forward current without reverse bias, t = 1 hour)		°C

1. $\frac{dPtot}{dTj} < \frac{1}{Rth(j-a)}$ condition to avoid thermal runaway for a diode on its own heatsink

Table 3. Thermal resistances

Symbol	Parameter	Value	Unit	
R _{th (j-c)}	Junction to case	Per diode Total	1.6 1.1	°C/W
R _{th(c)}	Coupling		0.5	°C/W

When the diodes 1 and 2 are used simultaneously:

 $\Delta T_{j}(diode \ 1) = P(diode1) \ x \ R_{th(j-c)}(Per \ diode) + P(diode2) \ x \ R_{th(c)}.$

Table 4. Static electrical ch	aracteristics (per diode)
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Symbol	Parameter	Test Con	Test Conditions		Тур.	Max.	Unit
I _R ⁽¹⁾	Povorso loakago ourront	$T_j = 25^\circ C$	V _V			650	μA
'R`´	R ⁽¹⁾ Reverse leakage current	T _j = 125° C	$V_{R} = V_{RRM}$		25	50	mA
		$T_j = 25^{\circ} \text{ C}$ $T_j = 125^{\circ} \text{ C}$ $I_F = 10 \text{ A}$	L _ 10 A		0.38	0.415	
V _F ⁽²⁾	Forward voltage drop				0.34	0.37	V
¥F` ∕	i orward voltage drop	T _j = 25° C	I _F = 20 A		0.46	0.50	v
		T _j = 125° C	F = 20 A		0.46	0.50	

1. Pulse test: $t_p = 5 \text{ ms}, \delta < 2\%$

2. Pulse test: t_p = 380 µs, δ < 2%

To evaluate the conduction losses use the following equation:

$$P = 0.31 \text{ x } I_{F(AV)} + 0.0095 I_{F}^{2}(RMS)$$



Figure 1. Average forward power dissipation versus average forward current (per diode)

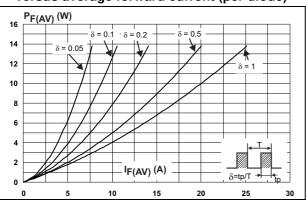
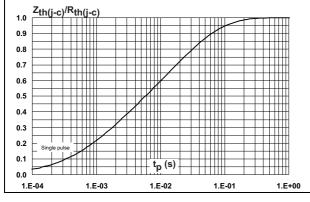


Figure 3. Relative variation of thermal impedance junction to case versus pulse duration



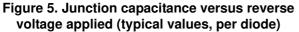


Figure 2. Average forward current versus ambient temperature (δ = 0.5, per diode)

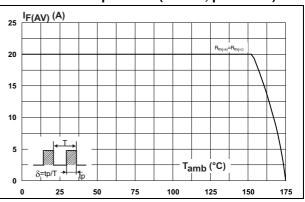


Figure 4. Reverse leakage current versus reverse voltage applied (typical values, per diode)

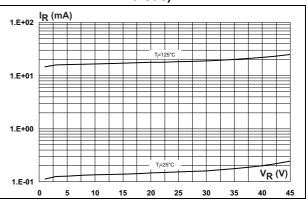
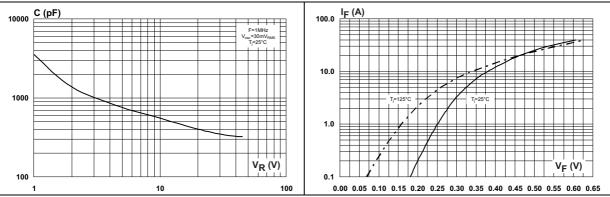


Figure 6. Forward voltage drop versus forward current (typical values, per diode)





80	R _{th(j}	a) (°0	C/W)						
70			_	Ероху	printed thickne	circuit bo ss: 35 ur	oard FR4, n		<u> </u>
60						+ +-	+ + +	_	
50									
40		\downarrow	_						
30								_	
20									
10							S(CII)) (cm²)	
0)	5	10	15	20	25	30	35	40

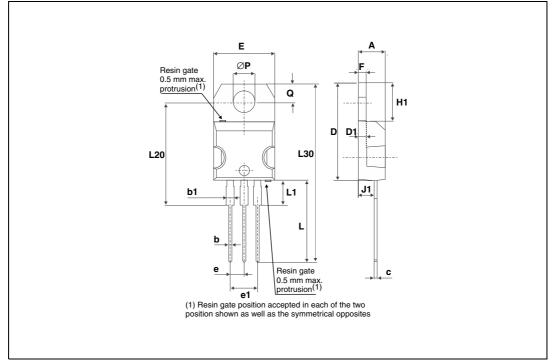
Figure 7. Thermal resistance junction to ambient versus copper surface under tab (typical values)

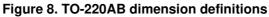


2 Package Information

- Epoxy meets UL94,V0
- Cooling method: by conduction (C)
- Recommended torque value: 0.4 to 0.6 N·m (TO-220AB)

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK[®] is an ST trademark.







Dimensions							
Ref.	Millime	ters	Incl	hes			
	Min.	Max.	Min.	Max.			
А	4.40	4.60	0.17	0.18			
b	0.61	0.88	0.024	0.035			
b1	1.14	1.70	0.045	0.067			
С	0.48	0.70	0.019	0.027			
D	15.25	15.75	0.60	0.62			
D1	1.27 ty	νp.	0.05 typ.				
E	10	10.40	0.39	0.41			
е	2.40	2.70	0.094	0.106			
e1	4.95	5.15	0.19	0.20			
F	1.23	1.32	0.048	0.052			
H1	6.20	6.60	0.24	0.26			
J1	2.40	2.72	0.094	0.107			
L	13	14	0.51	0.55			
L1	3.50	3.93	0.137	0.154			
L20	16.40 t	yp.	0.64	typ.			
L30	28.90 t	yp.	1.13	typ.			
ØP	3.75	3.85	0.147	0.151			
Q	2.65	2.95	0.104	0.116			

Table 5. TO-220AB dimension values



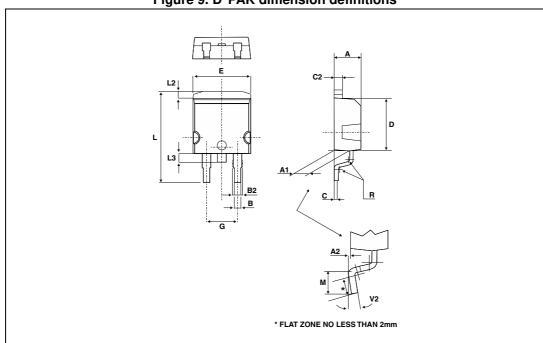


Figure 9. D²PAK dimension definitions

Table 6. D²PAK dimension values

	Dimensions							
Ref.	Millin	neters	Inches					
	Min.	Max.	Min.	Max.				
Α	4.40	4.60	0.173	0.181				
A1	2.49	2.69	0.098	0.106				
A2	0.03	0.23	0.001	0.009				
В	0.70	0.93	0.027	0.037				
B2	1.14	1.70	0.045	0.067				
С	0.45	0.60	0.017	0.024				
C2	1.23	1.36	0.048	0.054				
D	8.95	9.35	0.352	0.368				
E	10.00	10.40	0.393	0.409				
G	4.88	5.28	0.192	0.208				
L	15.00	15.85	0.590	0.624				
L2	1.27	1.40	0.050	0.055				
L3	1.30	1.75	0.051	0.069				
М	2.29	2.79	0.090	0.110				
R	0.40	typ.	0.016	δ typ.				
V2	0°	8°	0°	8°				



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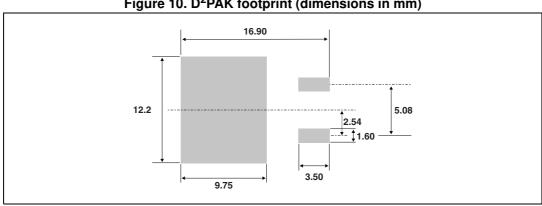


Figure 10. D²PAK footprint (dimensions in mm)



3 Ordering Information

Table 7. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
FERD40M45CT	FERD40M45CT	TO-220AB	2.2 g	50	Tube
FERD40M45CG-TR	FERD40M45CG	D ² PAK	1.8 g	500	Tape and reel

4 Revision history

Table 8. Document revision history

Date	Revision	Description of Changes
13-Nov-2013	1	Initial release



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